COMPLIANT





Dual SPDT Analog Switch

DESCRIPTION

The DG9636 is a CMOS, dual SPDT analog switch designed to operate from + 2.7 V to + 12 V, single supply. All control logic inputs have a guaranteed 1.65 V logic HIGH threshold when operation from a + 12 V power supply. This makes the DG9636 ideally suited to interface directly with low voltage micro-processor control signals.

Processed with high density CMOS technology, the DG9636 has a 83 Ω channel ON resistance while providing ultra low parasitic capacitance of 2 pF for $CS_{(OFF)}$ and 7 pF for $CD_{(ON)}$. Other performance features are: 720 MHz - 3 dB bandwidth, - 67 dB Cross Talk and - 58 dB Off isolation at 10 MHz frequency.

Key applications for the DG9636 are logic level translation, pulse generator, and high speed or low noise signal switching in precision instrumentations and portable device designs.

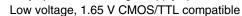
The DG9636 is available in space saving 1.4 mm x 1.8 mm miniQFN10 package.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with lead (Pb)-free device termination. The miniQFN-10 package has a nickel-palladium-gold device termination and is represented by the lead (Pb)-free "-E4" suffix to the ordering part number. The nickel-palladium-gold device terminations meet all JEDEC standards for reflow and MSL rating.

FEATURES

- Leakage current < 0.5 nA max. at 85 °C
- Low switch capacitance (C_{soff}, 2 pF typ.)
- R_{DS(on)} 83 Ω max.





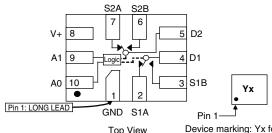
- 720 MHz, 3 dB bandwidth
- Excellent isolation and crosstalk performance (typ. > 60 dB at 10 MHz)
- Fully specified from 40 °C to 85 °C and 40 °C to + 125 °C
- · Latch-up current 300 mA per JESD78
- Lead (Pb)-free low profile miniQFN-10 (1.4 mm x 1.8 mm x 0.55 mm)
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- · High-end data acquisition
- · Medical instruments
- Precision instruments
- · High speed communications applications
- Automated test equipment
- · Sample and hold applications

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION

DG9636 miniQFN - 10L



Device marking: Yx for DG9636 x = Date/Lot Traceability Code

TRUTH TABLE		
Selec	ted Input	On Switches
A1	A0	DG9636
Х	0	D1 to S1A
Х	1	D1 to S1B
0	X	D2 to S2A
1	X	D2 to S2B

Document Number: 65159 S10-2012-Rev. B, 06-Sep-10



ORDERING INFORMATION							
Temp. Range	Package	Part Number					
- 40 °C to 125 °C	10 pin miniQFN	DG9636EN-T1-E4					
- 40 °C to 85 °C	10 pin miniQFN	DG9636DN-T1-E4					

Notes:

• - 40 °C to 85 °C datasheet limits apply.

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)							
Parameter		Limit	Unit				
V+ to GND		14	V				
Digital Inputs ^a , V _S , V _D		(V+) + 0.3 or 30 mA, whichever occurs first					
Continuous Current (Any Terminal)		30	mA				
Peak Current, S or D (Pulsed 1 ms, 10 %	Duty Cycle)	100	IIIA				
Storage Temperature		- 65 to 150	°C				
Power Dissipation (Package) ^b	10 pin miniQFN ^{c, d}	10 pin miniQFN ^{c, d} 208					
Thermal Resistance (Package) ^b	10 pin miniQFN	357	°C/W				

Notes:

- a. Signals on SX, DX, or AX exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC board.
- c. Derate 2.6 mW/°C above 70 °C.
- d. Manual soldering with iron is not recommended for leadless components. The miniQFN-10 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper lip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

SPECIFICATIONS FOR DUAL SUPPLIES										
	Test Conditions			- 40 °C to 125		o 125 °C	- 40 °C	to 85 °C		
Parameter	Symbol	Unless Otherwise Specified $V+ = 12 \text{ V}, V_{A0, A1} = 1.65 \text{ V}, 0.5 \text{ V}^a$	Temp.b	Typ. ^c	Min.d	Max. ^d	Min. ^d	Max. ^d	Unit	
Analog Switch										
Analog Signal Range ^e	V _{ANALOG}		Full			12		12	V	
On-Resistance	R _{DS(on)}	$I_S = 1 \text{ mA}, V_D = + 11.3 \text{ V}$	Room Full	83		110 140		110 125		
On-Resistance Match	ΔR _{ON}	$I_S = 1 \text{ mA}, V_D = + 11.3 \text{ V}$	Room Full	2		4 9		4 6	Ω	
On-Resistance Flatness	R _{FLATNESS}	$I_S = 1 \text{ mA}, V_D = 0.7 \text{ V}, 6.5 \text{ V}, 11.3 \text{ V}$	Room Full	33		45 55		45 50		
Switch Off	I _{S(off)}		Room Full	± 0.01	- 1 - 18	1 18	- 1 - 2	1 2		
Leakage Current	I _{D(off)}		Room Full	± 0.01	- 1 - 18	1 18	- 1 - 2	1 2	nA	
Channel On Leakage Current	I _{D(on)}	V+ = 12 V, V _D = V _S 11 V/1 V	Room Full	± 0.01	- 1 - 18	1 18	- 1 - 2	1 2		
Digital Control										
Input Current, V _{IN} Low	I _{IL}	V _{AX} = 0.5 V	Full	0.005	- 0.1	0.1	- 0.1	0.1	μA	
Input Current, V _{IN} High	I _{IH}	V _{AX} = 1.65 V	Full	0.005	- 0.1	0.1	- 0.1	0.1	μΑ	
Input Capacitance ^e	C _{IN}	f = 1 MHz	Room	3					pF	
Dynamic Characteristics	s									
Turn-On Time	t _{ON}		Room Full	30		70 90		70 80		
Turn-Off Time	t _{OFF}	t_{OFF} $R_L = 300 \Omega, C_L = 35 pF$ see figure 1, 2		15		55 75		55 65	ns	
Break-Before-Make	t _{BBM}		Room Full	15	5 2		5 2			
Charge Injection ^e	Q _{INJ}	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 1 \text{ nF}$	Room	23.5					рС	
Off Isolation ^e	OIRR	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$	Room	- 58					dB	
Bandwidth ^e	BW	$R_L = 50 \Omega$	Room	720					MHz	
Channel-to-Channel Crosstalk ^e	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$	Room	- 67					dB	



DG9636 Vishay Siliconix

SPECIFICATIONS FOR DUAL SUPPLIES											
		Test Conditions			- 40 °C t	o 125 °C	- 40 °C	to 85 °C	0		
Parameter	Symbol	Unless Otherwise Specified $V+ = 12 \text{ V}, V_{A0, A1} = 1.65 \text{ V}, 0.5 \text{ V}^a$	Temp.b	Typ. ^c	Min. ^d	Max. ^d	Min. ^d	Max. ^d	Unit		
Dynamic Characteristics	1										
Source Off Capacitance ^e	C _{S(off)}		Room	2							
Channel On Capacitance ^e	C _{D(on)}	f = 1 MHz	Room	7.7					pF		
Total Harmonic Distortion ^e	THD	Signal = 1 V_{RMS} , 20 Hz to 20 kHz, $R_L = 600 \Omega$	Room	0.01					%		
Power Supplies	Power Supplies										
Power Supply Current	l+	V = 0 V or V	Room Full	0.001		0.5 1		0.5 1			
Ground Current	I _{GND}	V _{IN} = 0 V, or V+	Room Full	- 0.001	- 0.5 - 1		- 0.5 - 1		μΑ		

		Test Conditions			- 40 °C to 125 °C		- 40 °C to 85 °C			
Parameter	Symbol	Unless Otherwise Specified $V+=5 \text{ V}, V_{A0, A1}=1.4 \text{ V}, 0.5 \text{ V}^a$	Temp.b	Typ. ^c	Min. ^d	Max. ^d	Min. ^d	Max.d	Unit	
Analog Switch				71						
Analog Signal Range ^e	V _{ANALOG}		Full			5		5	V	
On-Resistance	R _{DS(on)}	$I_S = 1 \text{ mA}, V_D = +3.5 \text{ V}$	Room Full	120		170 250		170 200	0	
On-Resistance Match	ΔR_{ON}	I _S = 1 mA, V _D = + 3.5 V	Room Full	3		5 12		5 10	Ω	
Switch Off	I _{S(off)}	V+ = 5.5 V,	Room Full	± 0.01	- 1 - 18	1 18	- 1 - 2	1 2		
Leakage Current	I _{D(off)}	$V_D = 1 \text{ V}/4.5 \text{ V}, V_S = 4.5 \text{ V}/1 \text{ V}$	Room Full	± 0.01	- 1 - 18	1 18	- 1 - 2	1 2	nA	
Channel On Leakage Current	I _{D(on)}	$V+ = 5.5 \text{ V}, V_S = V_D = 1 \text{ V}/4.5 \text{ V}$	Room Full	± 0.01	- 1 - 18	1 18	- 1 - 2	1 2		
Digital Control										
Input Current, V _{IN} Low	ΙL	V _{AX} = 0.5 V	Full	0.005	- 0.1	0.1	- 0.1	0.1	μΑ	
Input Current, V _{IN} High	Ι _Η	V _{AX} = 1.4 V	Full	0.005	- 0.1	0.1	- 0.1	0.1	μΑ	
Input Capacitance	C _{IN}	f = 1 MHz	Room	3					pF	
Dynamic Characteristics										
Turn-On Time	t _{ON}		Room Full	55						
Turn-Off Time	t _{OFF}	R_L = 300 Ω, C_L = 35 pF see figure 1, 2	Room Full	30					ns	
Break-Before-Make-Time	t _{BMM}		Room Full	36						
Charge Injection ^e	Q _{INJ}	$C_L = 1 \text{ nF, } R_{GEN} = 0 \Omega, V_{GEN} = 0 V$	Full	10					рC	
Off-Isolation ^e	OIRR	$f = 10 \text{ MHz}, R_1 = 50 \Omega, C_1 = 5 \text{ pF}$	Room	- 58					dB	
Crosstalke	X _{TALK}	$\frac{1}{1} = 10 \text{ MHz}, \text{ H}_{L} = 50 \text{ sz}, \text{ C}_{L} = 5 \text{ pr}$	Room	- 68					uБ	
Bandwidth ^e	BW	$R_L = 50 \Omega$	Room	610					MHz	
Total Harmonic Distortion ^e	THD	Signal = 1 V_{RMS} , 20 Hz to 20 kHz, $R_L = 600 \Omega$	Room	2.2					%	
Source Off Capacitance ^e	C _{S(off)}			2.1						
Channel On Capacitance ^e	C _{D(on)}	f = 1 MHz	Room	8.1					pF	
Power Supplies										
Power Supply Current	l+		Room	0.001		0.5		0.5		
Fower Supply Current	IT	$V_{IN} = 0 \text{ V, or V+}$	Full			1		1	μΑ	



SPECIFICATIONS	FOR SI	NGLE SUPPLY							
		Test Conditions			- 40 °C to	+ 125 °C	- 40 °C to	o + 85 °C	
Parameter	Symbol	Unless Otherwise Specified $V+=3 \text{ V}, V_{A0, A1}=1.4 \text{ V}, 0.5 \text{ V}^a$	Temp.b	Typ. ^c	Min.d	Max. ^d	Min. ^d	Max. ^d	Unit
Analog Switch									
Analog Signal Range ^e	V _{ANALOG}		Full			3		3	V
On-Resistance	R _{DS(ON)}	$I_S = 1 \text{ mA}, V_D = + 1.5 \text{ V}$	Room Full	200		245 325		245 290	Ω
On-Resistance Match	ΔR_{ON}	$I_S = 1 \text{ mA}, V_D = + 1.5 \text{ V}$	Room Full	5		6 13		6 11	32
Switch Off Leakage Current	I _{S(off)}	V+ = 3.3 V, V- = 0 V	Room Full	± 0.01	- 1 - 18	1 18	- 1 - 2	1 2	
(for 16 pin miniQFN)	I _{D(off)}	$V_D = 1 \text{ V/3 V}, V_S = 3 \text{ V/1 V}$	Room Full	± 0.01	- 1 - 18	1 18	- 1 - 2	1 2	nA
Channel On Leakage Current (for 16 pin miniQFN)	I _{D(on)}	$V_{+} = 3.3 \text{ V}, V_{-} = 0 \text{ V},$ $V_{S} = V_{D} = 1 \text{ V/3 V}$	Room Full	± 0.01	- 1 - 18	1 18	- 1 - 2	1 2	
Digital Control									
Input Current, V _{IN} Low	IL	V _{AX} = 0.5 V	Full	0.005	- 0.1	0.1	- 0.1	0.1	μΑ
Input Current, V _{IN} High	I _H	$V_{AX} = 1.4 \text{ V}$	Full	0.005	- 0.1	0.1	- 0.1	0.1	μΑ
Input Capacitance	C _{IN}	f = 1 MHz	Room	3.1					pF
Dynamic Characteristics	3								
Enable Turn-On Time	t _{ON}		Room Full	96					
Enable Turn-Off Time	t _{OFF}	$R_L = 300 \Omega$, $C_L = 35 pF$ see figure 1, 2	Room Full	60					ns
Break-Before-Make- Time	t _{BMM}		Room Full	77					
Charge Injection ^e	Q _{INJ}	$C_L = 1 \text{ nF, } R_{GEN} = 0 \Omega, V_{GEN} = 0 V$	Full	6.6					рC
Off-Isolation ^e	OIRR	$f = 10 \text{ MHz}, R_1 = 50 \Omega, C_1 = 5 \text{ pF}$	Room	- 57					dB
Crosstalk ^e	X _{TALK}	$\frac{1}{1} = 10 \text{ MHz}, \text{ H}_{L} = 50 \Omega, \text{ C}_{L} = 5 \text{ pr}$	Room	- 69					uБ
Bandwidth ^e	BW	$R_L = 50 \Omega$	Room	525					MHz
Total Harmonic Distortion ^e	THD	Signal = 1 V_{RMS} , 20 Hz to 20 kHz, $R_L = 600 \Omega$	Room	2.2					%
Source Off Capacitance ^e	C _{S(off)}			2.1					
Channel On Capacitance ^e	C _{D(on)}	f = 1 MHz	Room	8.3					pF
Power Supplies									
Power Supply Current	l+	V = 0.V or V:	Room Full	0.001		0.5 1		0.5 1	
Ground Current	I _{GND}	$V_{IN} = 0 \text{ V, or V+}$	Room Full	- 0.001	- 0.5 - 1		- 0.5 - 1		μΑ

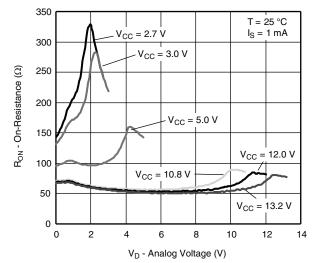
Notes:

- a. V_{IN} = input voltage to perform proper function.
- b. Room = 25 °C, Full = as determined by the operating temperature.
- c. Typical value are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- e. Guaranteed by design, not subject to production test.

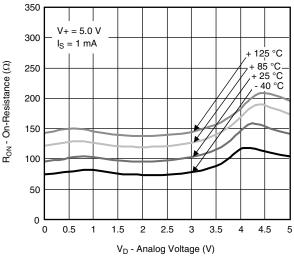
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



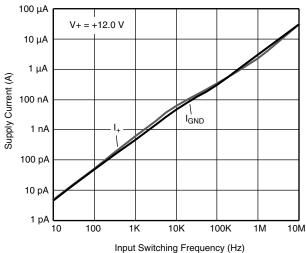
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



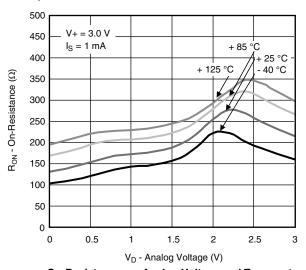
On-Resistance vs. Single Supply Voltage



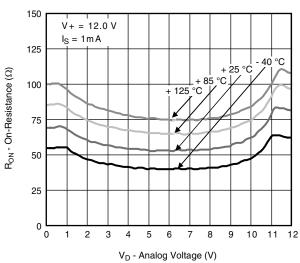
On-Resistance vs. Analog Voltage and Temperature



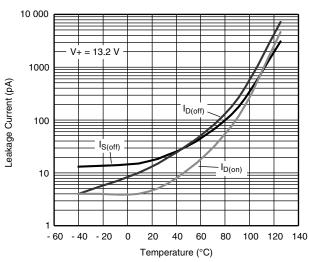
Supply Current vs. Input Switching Frequency



On-Resistance vs. Analog Voltage and Temperature



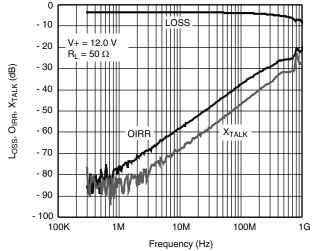
On-Resistance vs. Analog Voltage and Temperature

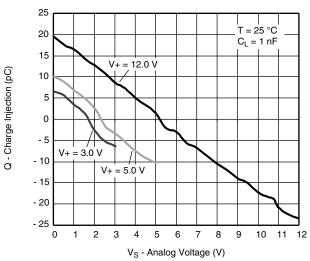


Leakage Current vs. Temperature

VISHAY.

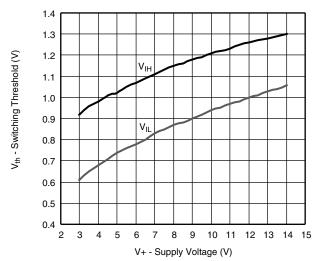
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





Insertion Loss, Off-Isolation, Crosstalk vs. Frequency

Charge Injection vs. Analog voltage



Switching Threshold vs. Supply Voltage



TEST CIRCUITS

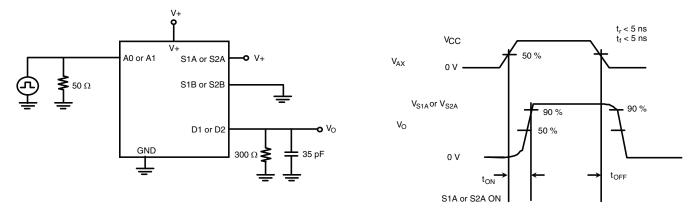


Figure 1. Enable Switching Time

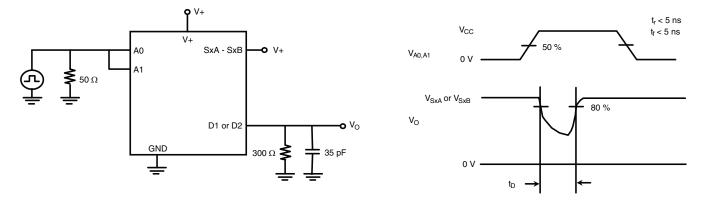


Figure 2. Break-Before-Make

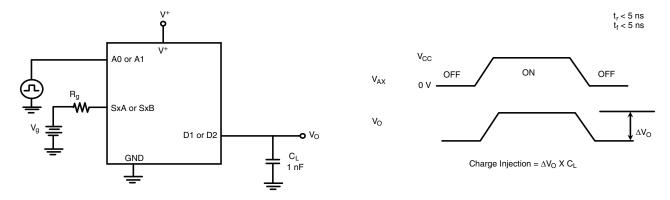


Figure 3. Charge Injection

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TEST CIRCUITS

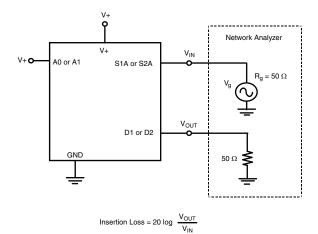


Figure 4. Insertion Loss

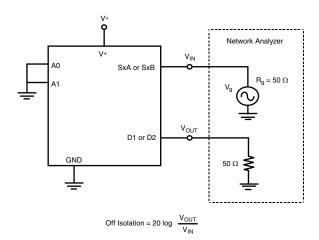


Figure 5. Off-Isolation

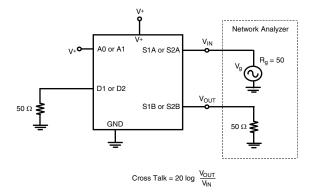


Figure 6. Crosstalk

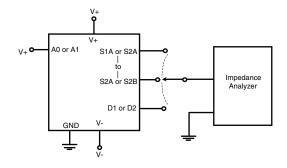
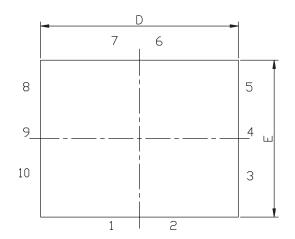
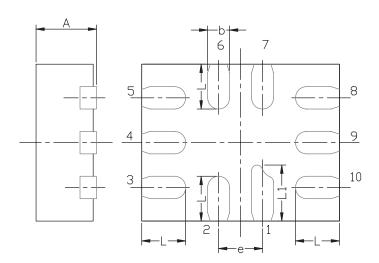


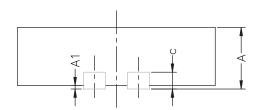
Figure 7. Source/Drain Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppq?65159.

MINI QFN-10L CASE OUTLINE







DIM	M	IILLIMETER	IS .	INCHES				
DIIVI	MIN.	NAM.	MAX.	MIN.	NAM.	MAX.		
Α	0.50	0.55	0.60	0.0197	0.0217	0.0236		
A1	0.00	-	0.05	0.000	-	0.002		
b	0.15	0.20	0.25	0.006	0.008	0.010		
С		0.15 REF	•		0.006 REF			
D	1.75	1.80	1.85	0.069	0.073			
Е	1.35	1.40	1.45	0.053	0.055	0.057		
е		0.40 BSC		0.016 BSC				
L	0.35	0.40	0.45	0.014	0.016	0.018		
L1	0.45	0.50	0.55	0.0177	0.0197	0.0217		

ECN T-07039-Rev. A, 12-Feb-07

DWG: 5957





Vishay

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